

**Gate resistor installed  
Dual N-channel MOSFET**

**KFC6B21150L  
Data Sheet**

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## 1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET  
For lithium-ion secondary battery protection circuits

## 2. FEATURES

- Low source-source ON resistance: RSS (on) typ. = 4.0 mΩ (VGS = 4.5 V)
  - CSP (Chip Size Package)
  - RoHS compliant (EU RoHS / MSL: Level 1 compliant)

### **3. MARKING SYMBOL: 16**

#### **4. PACKAGING**

Embossed type (Thermo-compression sealing): 10,000 pcs / reel (standard)

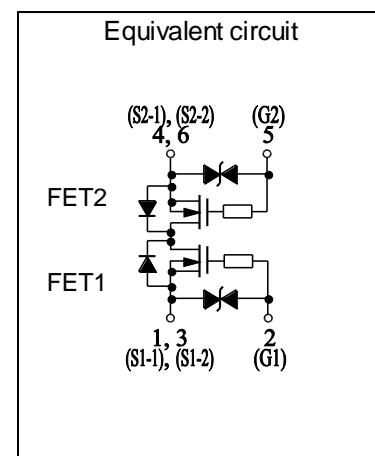
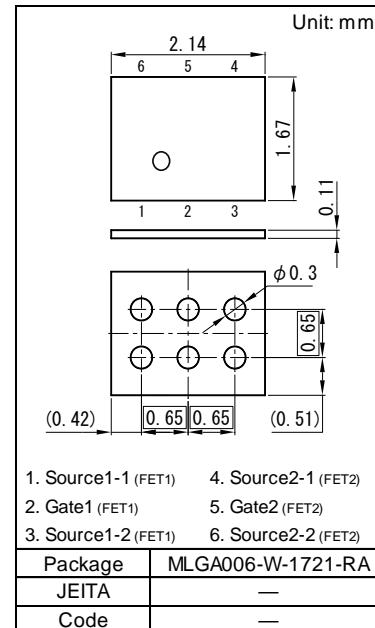
## 5. ABSOLUTE MAXIMUM RATINGS $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	12	V
Gate-source Voltage	VGS	±10.5	V
Source Current	DC	IS1 *1	8
		IS2 *2	17
	Pulsed	ISp *3	80
Total Power Dissipation	DC	PD1 *1	0.45
		PD2 *2	2.1
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

## 6. THERMAL CHARACTERISTICS $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Thermal Resistance ( ch-a )	Rth1 <sup>*1</sup>	278	°C / W
	Rth2 <sup>*2</sup>	59	

Note \*1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm)  
           using the minimum recommended pad size (36 $\mu$ m Copper).  
   \*2 Mounted on Ceramic substrate (70 mm x 70 mm x t1.0 mm).  
   \*3 t = 10  $\mu$ s, Duty Cycle  $\leq$  1 %



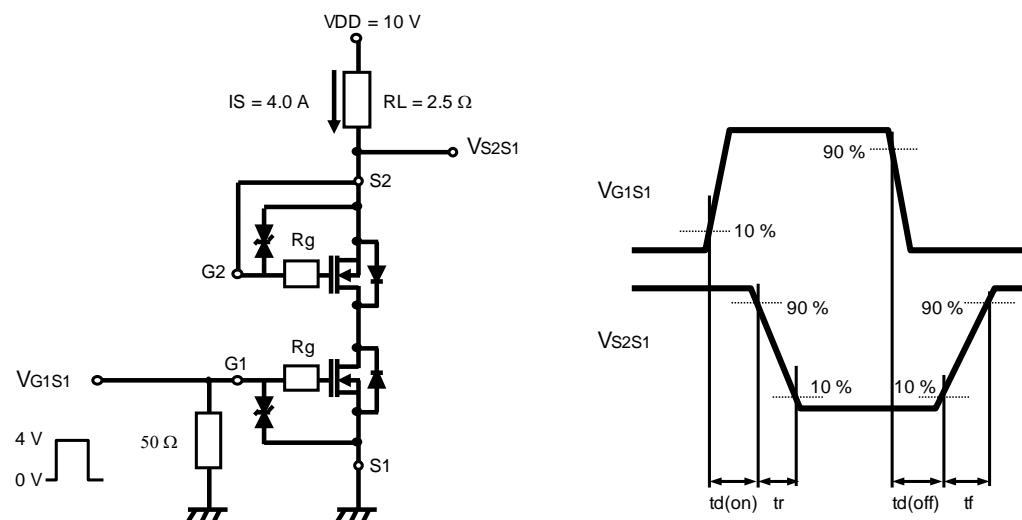
7. ELECTRICAL CHARACTERISTICS  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	$IS = 1 \text{ mA}, VGS = 0 \text{ V}$	12			V
Zero Gate Voltage Source Current	ISSS	$VSS = 12 \text{ V}, VGS = 0 \text{ V}$			1.0	$\mu\text{A}$
Gate-source Leakage Current	IGSS1	$VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$			$\pm 10$	$\mu\text{A}$
	IGSS2	$VGS = \pm 5 \text{ V}, VSS = 0 \text{ V}$			$\pm 1.0$	$\mu\text{A}$
Gate-source Threshold Voltage	Vth	$IS = 0.84 \text{ mA}, VSS = 10 \text{ V}$	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	$IS = 4.0 \text{ A}, VGS = 4.5 \text{ V}$	3.0	4.0	5.1	$\text{m}\Omega$
	RSS(on)2	$IS = 4.0 \text{ A}, VGS = 3.8 \text{ V}$	3.2	4.3	5.5	
	RSS(on)3	$IS = 4.0 \text{ A}, VGS = 3.1 \text{ V}$	3.5	4.8	6.8	
	RSS(on)4	$IS = 4.0 \text{ A}, VGS = 2.5 \text{ V}$	3.8	5.9	10.0	
Body Diode Forward Voltage	VF(s-s)	$IF = 4.0 \text{ A}, VGS = 0 \text{ V}$		0.8	1.2	V
Input Capacitance <sup>*1</sup>	Ciss	$VSS = 10 \text{ V}, VGS = 0 \text{ V}, f = 1 \text{ kHz}$		2760		$\text{pF}$
Output Capacitance <sup>*1</sup>	Coss			450		
Reverse Transfer Capacitance <sup>*1</sup>	Crss			390		
Turn-on Delay Time <sup>*1,*2</sup>	td(on)	$VDD = 10 \text{ V}, VGS = 0 \text{ to } 4 \text{ V}$		4.1		$\mu\text{s}$
Rise Time <sup>*1,*2</sup>	tr		$IS = 4.0 \text{ A}$	5.2		
Turn-off Delay Time <sup>*1,*2</sup>	td(off)	$VDD = 10 \text{ V}, VGS = 4 \text{ to } 0 \text{ V}$		12.9		$\mu\text{s}$
Fall Time <sup>*1,*2</sup>	tf		$IS = 4.0 \text{ A}$	8.3		
Total Gate Charge <sup>*1</sup>	Qg	$VDD = 10 \text{ V}$		26		$\text{nC}$
Gate-source Charge <sup>*1</sup>	Qgs		$VGS = 0 \text{ to } 4 \text{ V}$	9		
Gate-drain Charge <sup>*1</sup>	Qgd		$IS = 4.0 \text{ A}$	8		

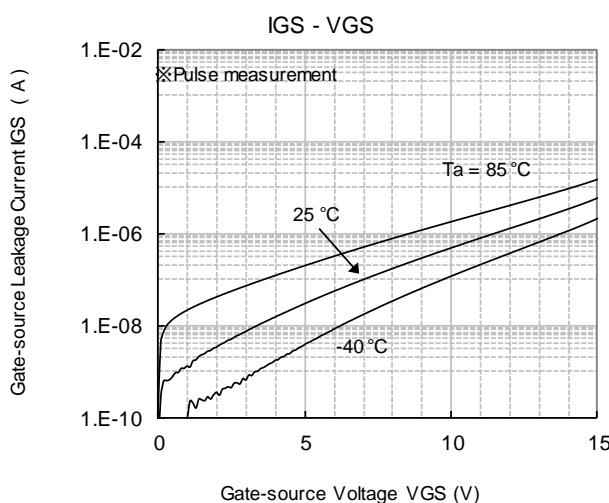
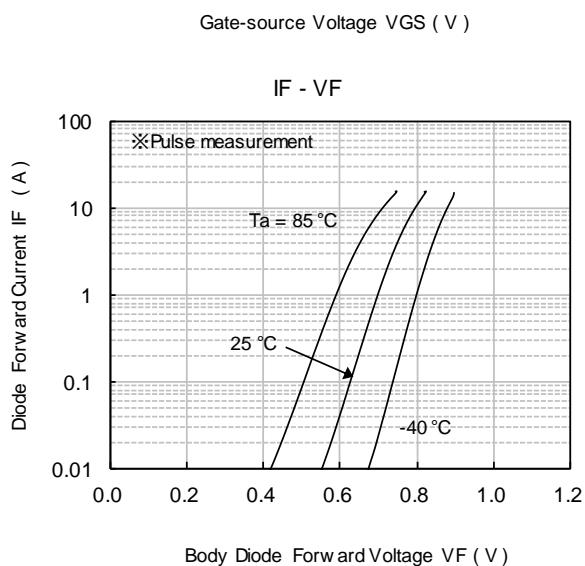
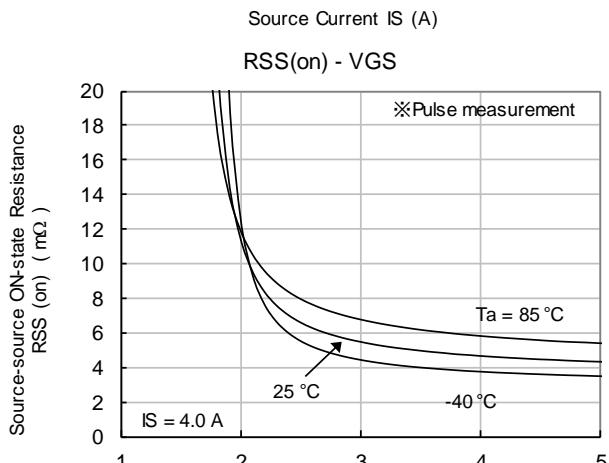
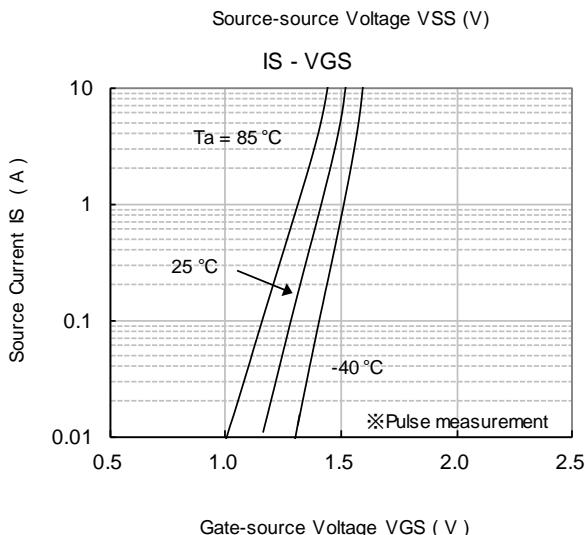
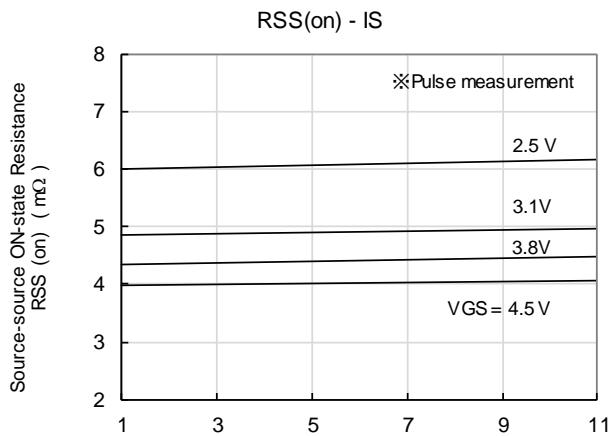
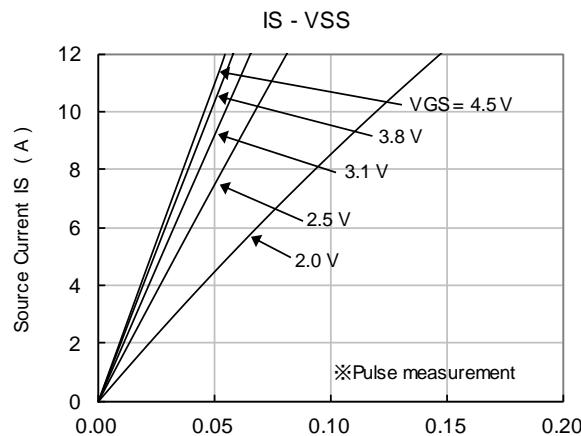
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

<sup>\*1</sup> Guaranteed by design, not subject to production testing

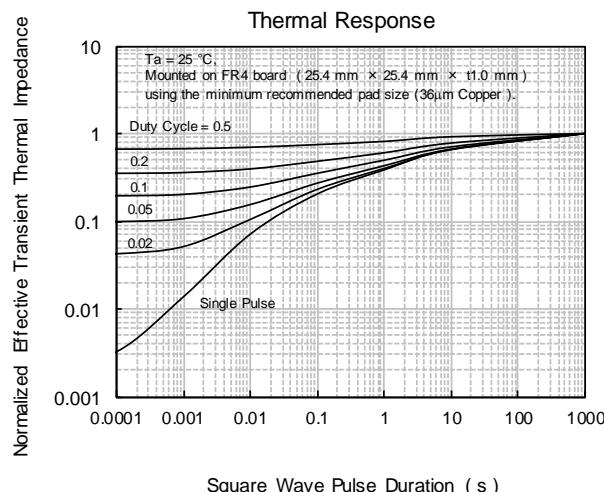
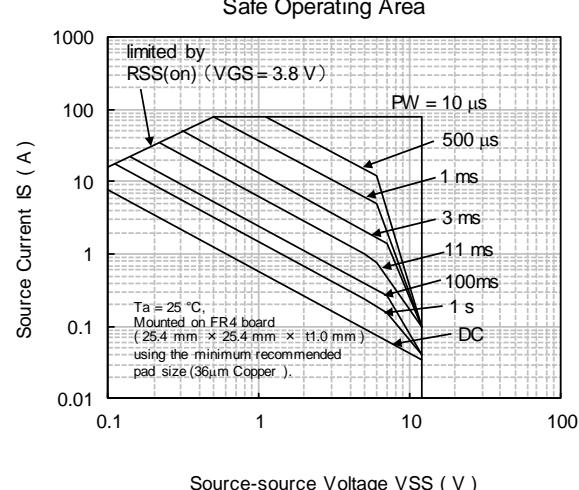
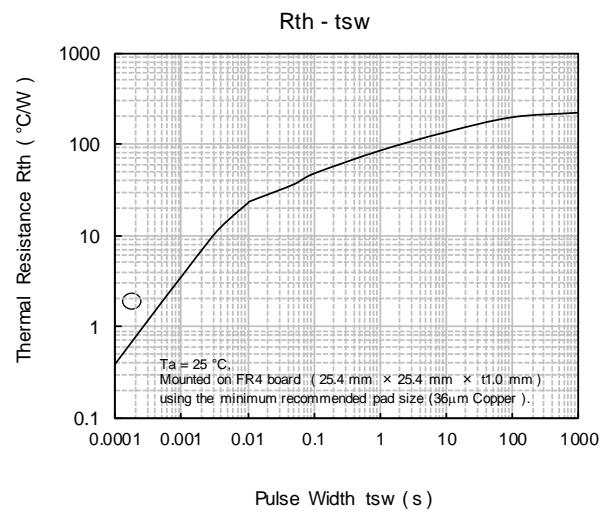
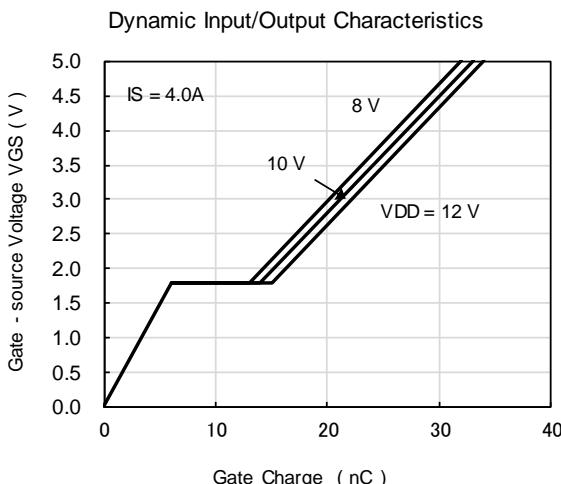
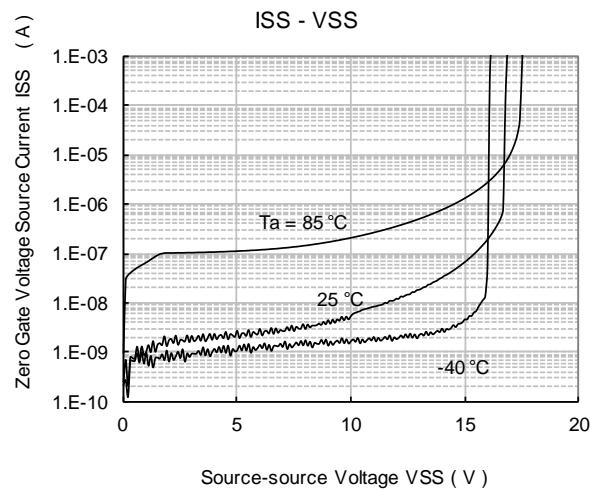
<sup>\*2</sup> Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

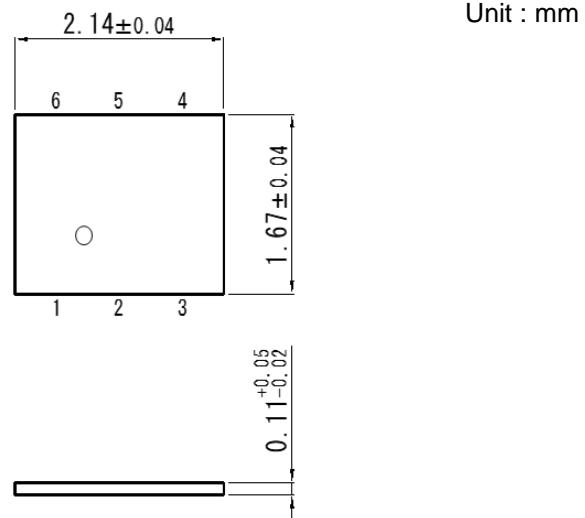


## 8. TECHNICAL DATA (Reference)

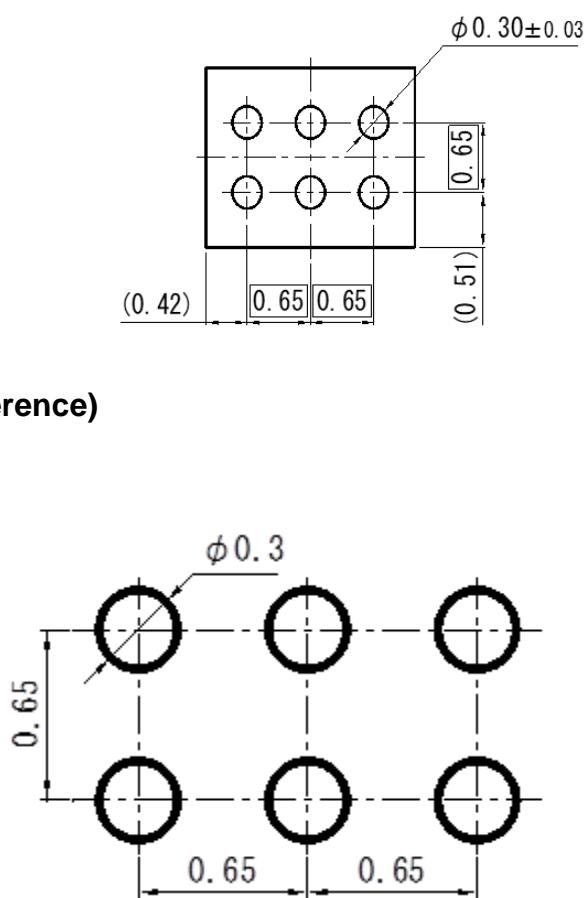


## TECHNICAL DATA (Reference)



**9. OUTLINE****10. LAND PATTERN (Reference)**

Unit: mm



**12. REVISION HISTORY**

Date	Revision	Description
2021.2.4	1.00	1. initially issued.

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